

Microsemi Corp.
The diode experts

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SCOTTSDALE, AZ

**1N897 - 1N902,
1N3064M, 1N3069M,
1N3206, 1N3207,
MC914, MC914A,
MC916, MC916A,
MC001, MC001A,
MC002**

FEATURES

- Microminiature package.
- Fast recovery.
- Stable surface films integrally bonded to the device crystal.
- Meet or exceed requirements of MIL-S-19500/195 (1N 3206) and MIL-S-19500/230 (1N 3207).

MAXIMUM RATINGS

Operating Temperature: -65°C to $+175^{\circ}\text{C}$.
Storage Temperature: -65°C to $+175^{\circ}\text{C}$.
Power Dissipation: 100 mW @ 25°C Au plated kovar leads.

ELECTRICAL CHARACTERISTICS

TYPE	BREAKDOWN VOLTAGE (MIN.) @ 100 μA V_{BR}	FORWARD CURRENT (MIN.) @ 1.0V I_{F}	REVERSE CURRENT (MAX.) I_{R} @ V_{R}		TEST VOLTAGE V_{R}	CAPACITANCE (MAX.) @ 0 V C_0	REVERSE RECOVERY (MAX.) (NOTES BELOW) t_{rr}
	VOLTS	mA	μA		VOLTS	pF	n sec.
			25°C	100°C			
1N897	50	5	0.1	20.0	-40V	—	100K n in .1 μsec (1)
1N898	50	100	0.025	5.0	-10V	—	—
1N899	100	5	5.0	20.0	-40V	—	100K n in .3 μsec (1)
1N900	100	50	0.025	5.0	-10V	—	—
1N901	100	100	0.1	20.0	-80V	—	100K n in .3 μsec (1)
1N902	200	10	0.025	5.0	-10V	—	—
MC914	100	10	0.1	20.0	-80V	—	100K n in .3 μsec (1)
MC914A	100	20	0.025	5.0	-10V	—	—
MC916	100	10	0.1	20.0	-80V	—	100K n in .3 μsec (1)
MC916A	100	20	0.025	5.0	-10V	—	—
MC001	75	10	0.5	20.0	-80V	—	100K n in .3 μsec (1)
MC001A	75	20	0.025	5.0	-10V	—	—
MC002	200	100	0.1	20.0	-80V	—	100K n in .3 μsec (1)
1N3064M	75 (@ 5mA)	10	0.1	20.0	-80V	—	100K n in .3 μsec (1)
1N3069M	65 (@ 5mA)	50	0.1	20.0	-80V	—	100K n in .3 μsec (1)
1N3206	100	10	0.025	50.0(5)	-20V	4.0	200K n in .3 μsec (1)
JAN N3206	100	10	0.025	30.0(5)	-20V	2.0	4.0(2)
			0.5		-20V	2.0	4.0(2)
			0.05	60.0(5)	-80V	15.0	6.0(2)
JAN N3207	60	150	0.05	10.0	-20V	6.0	6.0(2)
1N3207	60	150	0.05	10.0	-20V	6.0	6.0(2)

NOTES:

- (1) JAN256 Recovery Test Circuit Conditions 5mA to -40V.
- (2) Recovery to 1.0 mA reverse, switching from 10 mA forward to -6.0 Volts. $R_{\text{L}} = 100$ ohms.
- (3) Recovery to 1.0 mA reverse, switching from 30 mA forward to 30 mA reverse. $R_{\text{L}} = 150$ ohms.
- (4) Recovery to 1.0 mA reverse, switching from 10 mA forward to 10 mA reverse. $R_{\text{L}} = 100$ ohms.
- (5) I_{R} measured at 150°C .

PELLET DIODES

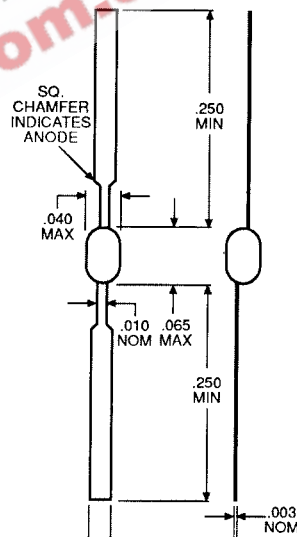


FIGURE 1
PACKAGE "H"

MECHANICAL CHARACTERISTICS

Case: Ultra stable epoxy encapsulation.
Lead Material: Gold plated kovar or gold plated silver.
Markings: EIA color code bands.
Polarity: Color bands on cathode lead.

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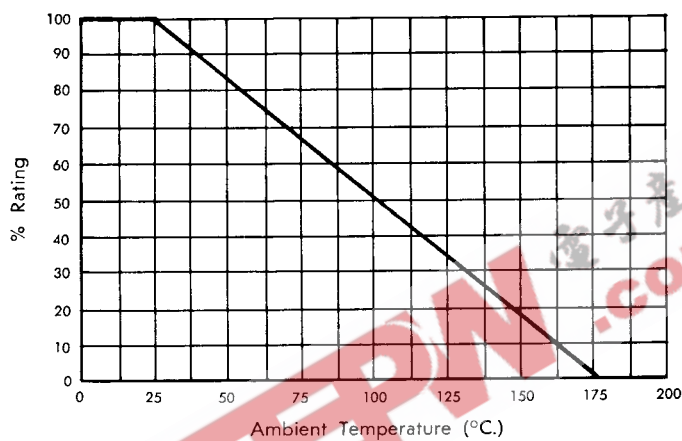


FIGURE 2
TEMPERATURE DERATING CURVE

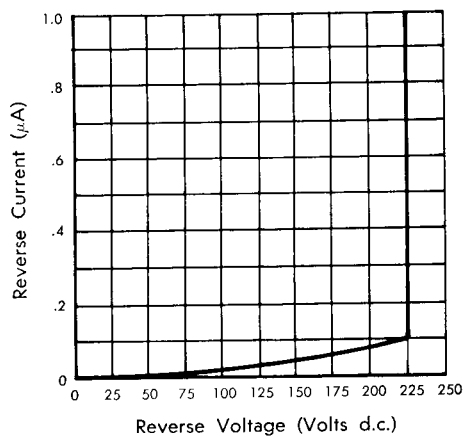


FIGURE 3
TYPICAL REVERSE
CHARACTERISTICS (25°C)

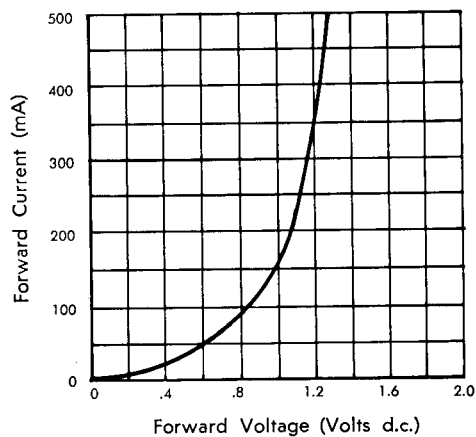


FIGURE 4
TYPICAL FORWARD CURRENT
CHARACTERISTICS (25°C)